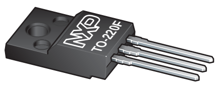



# PSMN016-100XS

## N-channel 100V 16 mΩ standard level MOSFET in TO220F (SOT186A)

Rev. 4 — 6 March 2012 **Product data sheet**

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220F (SOT186A) package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Isolated package
- Suitable for standard level gate drive

### 1.3 Applications

- AC-to-DC power supply equipment
- Motor control
- Server power supplies
- Synchronous rectification

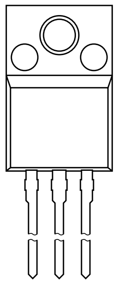
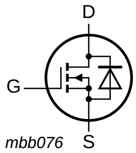
### 1.4 Quick reference data

**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | $T_j \geq 25$ °C; $T_j \leq 175$ °C | - | - | 100 | V |
| $I_D$ | drain current | $T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 1 | - | - | 32.1 | A |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25$ °C; see Figure 2 | - | - | 46.1 | W |
| **Static characteristics** | | | | | | |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS} = 10$ V; $I_D = 10$ A; $T_j = 25$ °C; see Figure 12; see Figure 13 | - | 13 | 16 | mΩ |
| **Dynamic characteristics** | | | | | | |
| $Q_{GD}$ | gate-drain charge | $V_{GS} = 10$ V; $I_D = 10$ A; $V_{DS} = 50$ V; see Figure 14; see Figure 15 | - | 14.2 | - | nC |
| $Q_{G(tot)}$ | total gate charge | | - | 46.2 | - | nC |
| **Avalanche ruggedness** | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 32.1$ A; $V_{sup} \leq 100$ V; unclamped; $R_{GS} = 50$ Ω; see Figure 3 | - | - | 138 | mJ |

## 2. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|---|---|---|---|---|
| 1 | G | gate | <br>SOT186A (TO-220F) |  |
| 2 | D | drain | | |
| 3 | S | source | | |
| mb | | mounting base; isolated | | |

## 3. Ordering information

**Table 3. Ordering information**

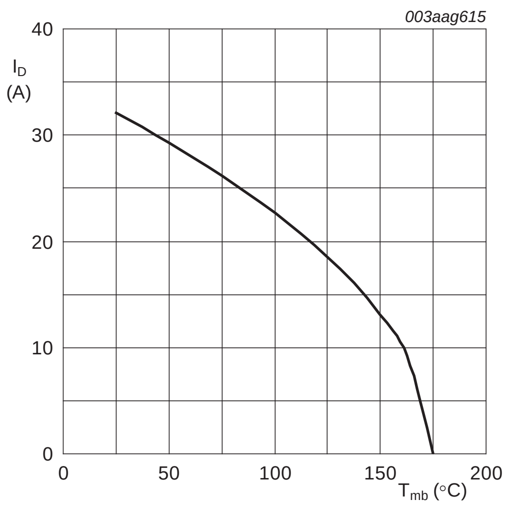
| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| PSMN016-100XS | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

# 4. Limiting values

**Table 4. Limiting values**

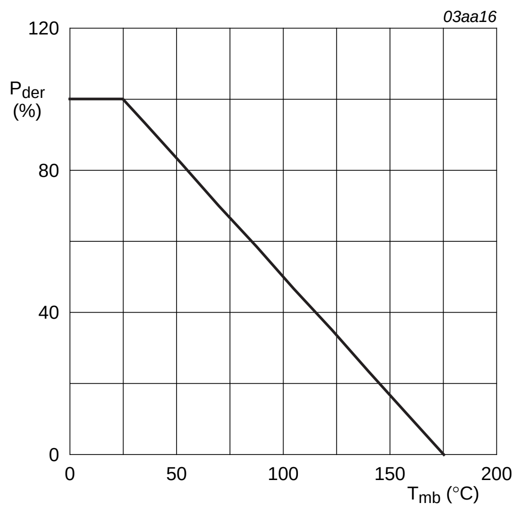
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | $T_j \geq 25$ °C; $T_j \leq 175$ °C | - | 100 | V |
| $V_{DGR}$ | drain-gate voltage | $T_j \geq 25$ °C; $T_j \leq 175$ °C; $R_{GS} = 20$ kΩ | - | 100 | V |
| $V_{GS}$ | gate-source voltage | | -20 | 20 | V |
| $I_D$ | drain current | $V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 1 | - | 32.1 | A |
| | | $V_{GS} = 10$ V; $T_{mb} = 100$ °C; see Figure 1 | - | 22.7 | A |
| $I_{DM}$ | peak drain current | pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; see Figure 4 | - | 128 | A |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25$ °C; see Figure 2 | - | 46.1 | W |
| $T_{stg}$ | storage temperature | | -55 | 175 | °C |
| $T_j$ | junction temperature | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | - | 260 | °C |
| **Source-drain diode** | | | | | |
| $I_S$ | source current | $T_{mb} = 25$ °C | - | 38.5 | A |
| $I_{SM}$ | peak source current | pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C | - | 128 | A |
| **Avalanche ruggedness** | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; $I_D = 32.1$ A; $V_{sup} \leq 100$ V; unclamped; $R_{GS} = 50$ Ω; see Figure 3 | - | 138 | mJ |



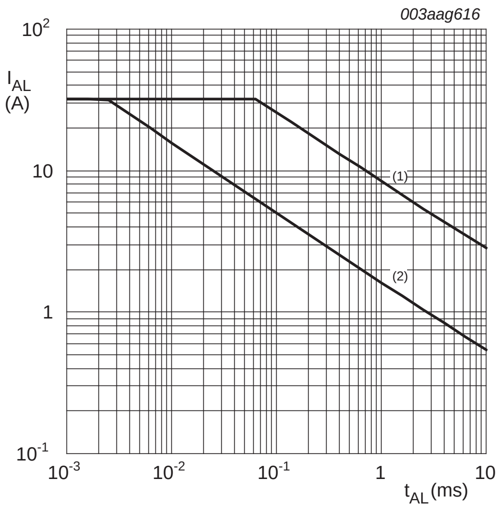

$$V_{GS} \geq 10V$$

**Fig 1. Continuous drain current as a function of mounting base temperature**



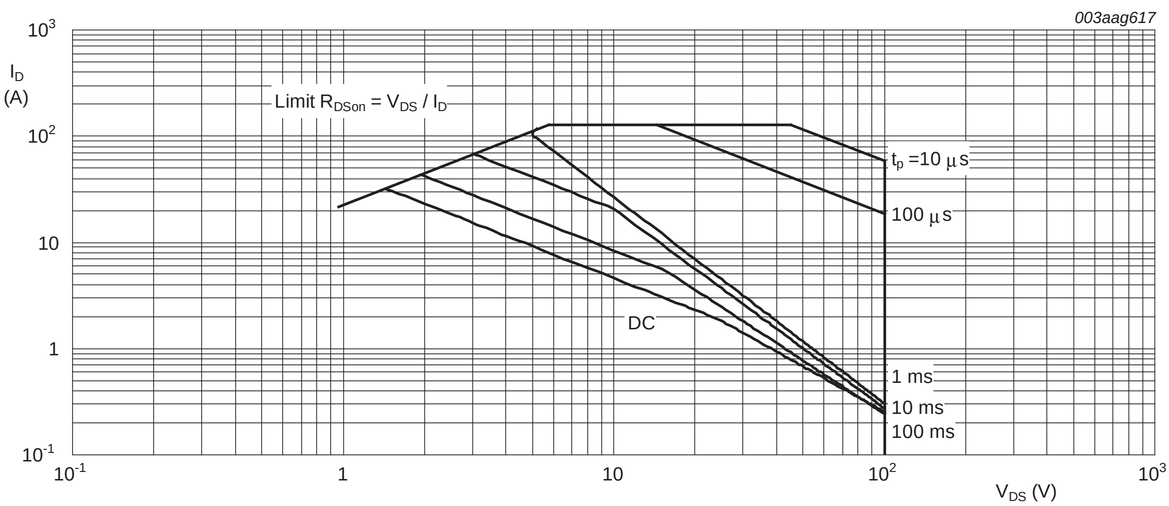

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\,\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**




(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 130°C$

**Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time**




$T_{mb} = 25°C$; $I_{DM}$ *is a single pulse*

**Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 5 | - | 3 | 3.25 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | vertical in free air | - | 55 | - | K/W |

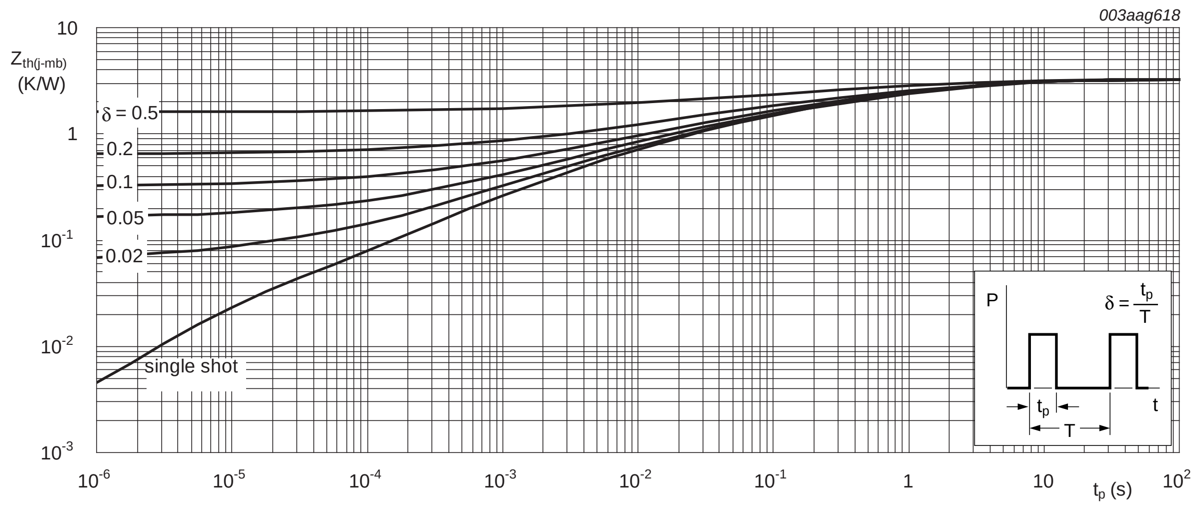



**Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Isolation characteristics

**Table 6. Isolation characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $C_{isol}$ | isolation capacitance | f = 1 MHz | - | 10 | - | pF |
| $V_{isol(RMS)}$ | RMS isolation voltage | 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; sinusoidal waveform; clean and dust free | - | - | 2500 | V |

# 7. Characteristics

**Table 7. Characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C | 100 | - | - | V |
| | | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C | 90 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 25 °C; see Figure 10; see Figure 11 | 2 | 3 | 4 | V |
| | | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 175 °C; see Figure 10 | 1 | - | - | V |
| | | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = -55 °C; see Figure 10 | - | - | 4.6 | V |
| $I_{DSS}$ | drain leakage current | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C | - | - | 5 | µA |
| | | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 100 °C | - | - | 100 | µA |
| $I_{GSS}$ | gate leakage current | $V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C | - | 2 | 100 | nA |
| | | $V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C | - | 2 | 100 | nA |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; see Figure 12; see Figure 13 | - | 13 | 16 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 100 °C; see Figure 13 | - | 22.8 | 28 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 175 °C; see Figure 13 | - | 36.4 | 44.8 | mΩ |
| $R_G$ | internal gate resistance (AC) | f = 1 MHz | - | 0.9 | - | Ω |
| **Dynamic characteristics** | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D$ = 10 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see Figure 14; see Figure 15 | - | 46.2 | - | nC |
| $Q_{GS}$ | gate-source charge | | - | 10.4 | - | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | - | 7.1 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | - | 3.3 | - | nC |
| $Q_{GD}$ | gate-drain charge | | - | 14.2 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D$ = 10 A; $V_{DS}$ = 50 V; see Figure 14; see Figure 15 | - | 4.5 | - | V |
| $C_{iss}$ | input capacitance | $V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_j$ = 25 °C; see Figure 16; see Figure 17 | - | 2404 | - | pF |
| $C_{oss}$ | output capacitance | $V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_j$ = 25 °C; see Figure 16 | - | 189 | - | pF |
| $C_{rss}$ | reverse transfer capacitance | $V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_j$ = 25 °C; see Figure 16; see Figure 17 | - | 113 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS}$ = 50 V; $R_L$ = 5 Ω; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 4.7 Ω; $T_j$ = 25 °C | - | 16 | - | ns |
| $t_r$ | rise time | | - | 16 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 39 | - | ns |
| $t_f$ | fall time | | - | 18 | - | ns |

**Table 7. Characteristics** *...continued*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Source-drain diode** | | | | | | |
| $V_{SD}$ | source-drain voltage | $I_S$ = 10 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C | - | 0.8 | 1.2 | V |
| $t_{rr}$ | reverse recovery time | $I_S$ = 10 A; $dI_S/dt$ = -100 A/µs; $V_{GS}$ = 0 V; $V_{DS}$ = 50 V | - | 54 | - | ns |
| $Q_r$ | recovered charge | | - | 126 | - | nC |

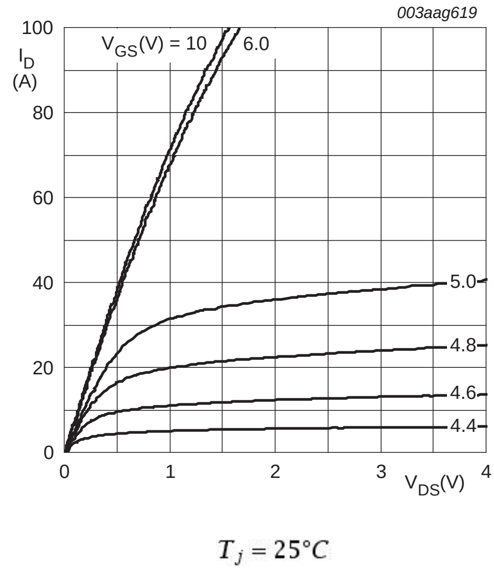



**Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values**

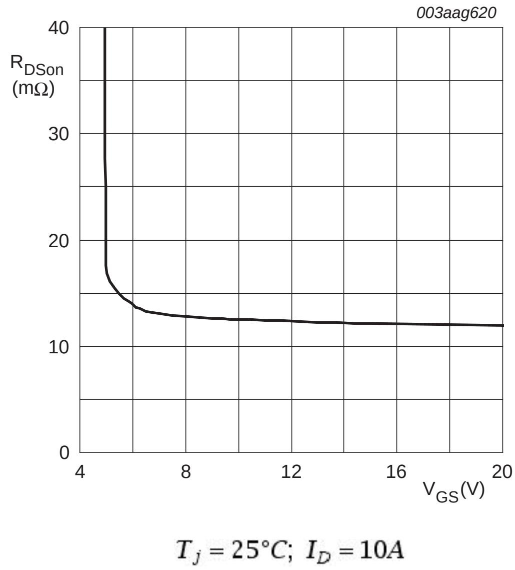



**Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

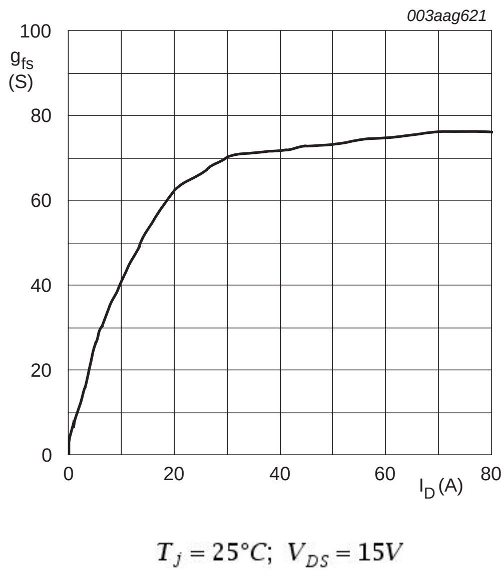



**Fig 8. Forward transconductance as a function of drain current; typical values**

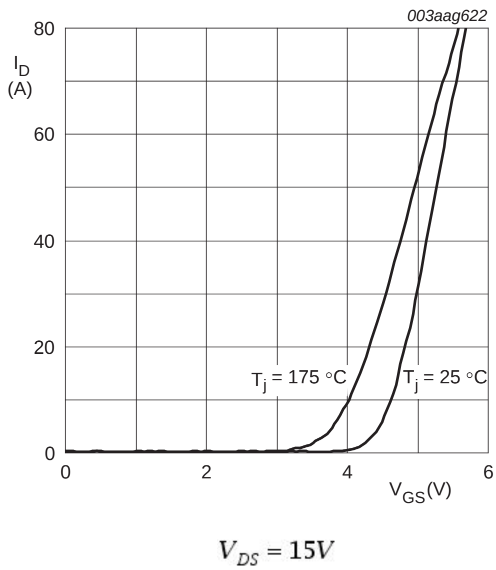
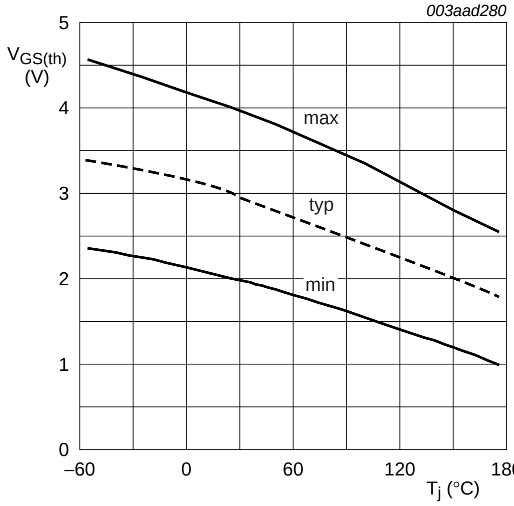
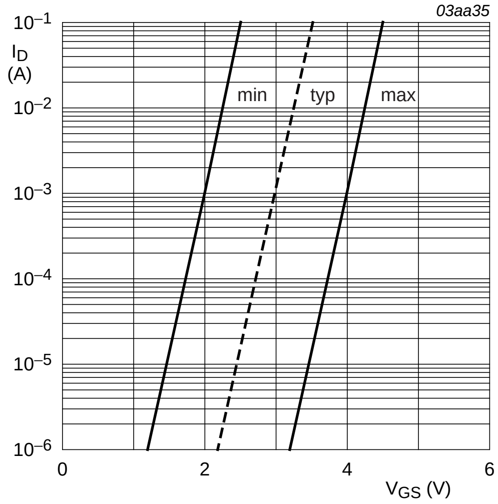



**Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



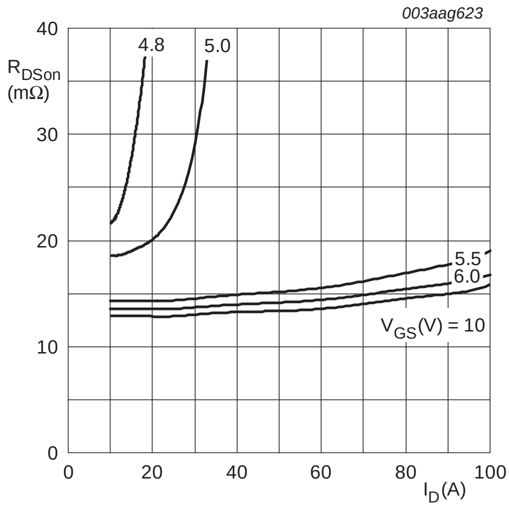

$I_D = 1\,\text{mA};\ V_{DS} = V_{GS}$

**Fig 10. Gate-source threshold voltage as a function of junction temperature**



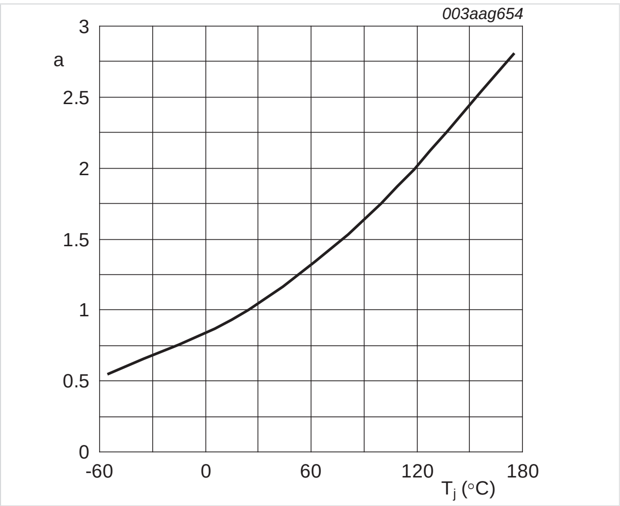

$T_j = 25\,°C; V_{DS} = 5V$

**Fig 11. Sub-threshold drain current as a function of gate-source voltage**




$T_j = 25°C$

**Fig 12. Drain-source on-state resistance as a function of drain current; typical values**




$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

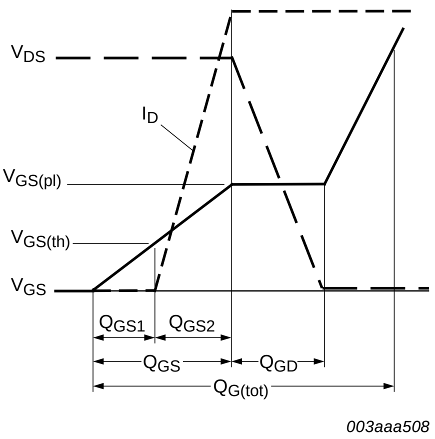
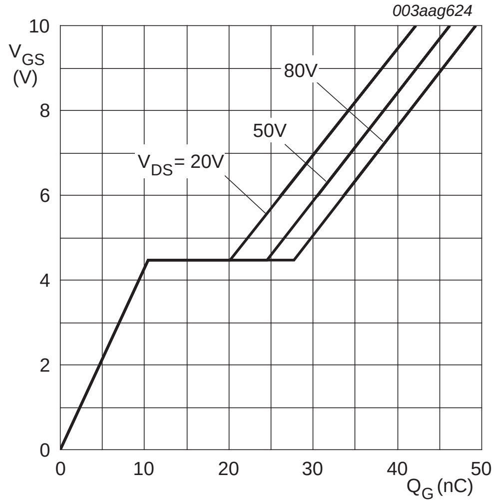
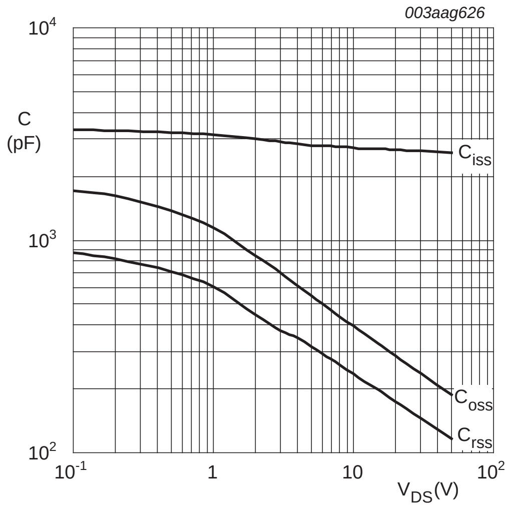



Fig 14. Gate charge waveform definitions



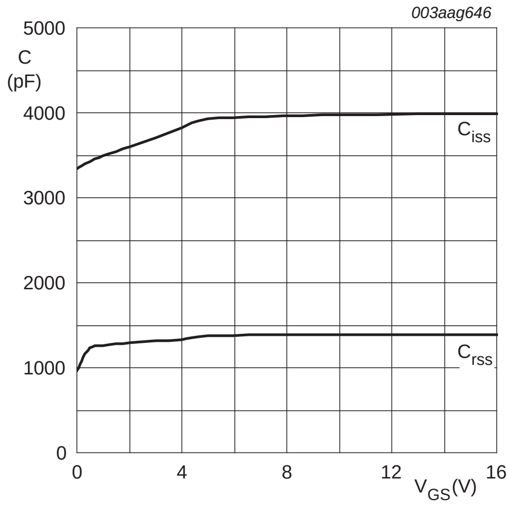

$T_j = 25°C;\ I_D = 10A$

Fig 15. Gate-source voltage as a function of gate charge; typical values




$V_{GS} = 0V;\ f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



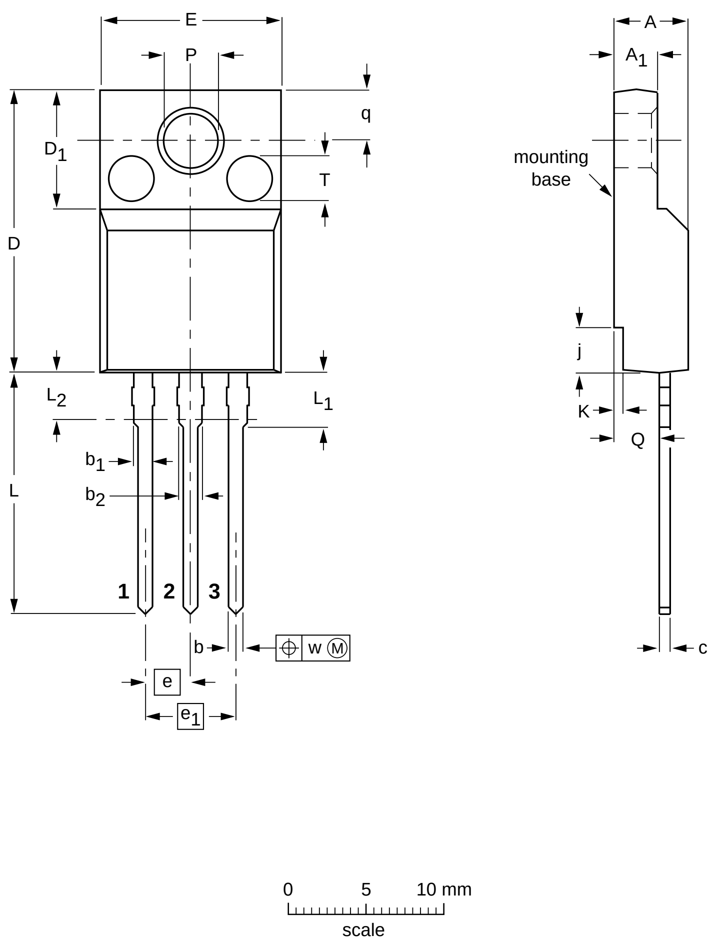

$f = 1MHz;\ V_{DS} = 0V$

Fig 17. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

## 8. Package outline

**Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'**

**SOT186A**




**DIMENSIONS (mm are the original dimensions)**

| UNIT | A | $A_1$ | b | $b_1$ | $b_2$ | c | D | $D_1$ | E | e | $e_1$ | j | K | L | $L_1$ | $L_2$(1) max. | P | Q | q | T(2) | w |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 4.6<br>4.0 | 2.9<br>2.5 | 0.9<br>0.7 | 1.1<br>0.9 | 1.4<br>1.0 | 0.7<br>0.4 | 15.8<br>15.2 | 6.5<br>6.3 | 10.3<br>9.7 | 2.54 | 5.08 | 2.7<br>1.7 | 0.6<br>0.4 | 14.4<br>13.5 | 3.30<br>2.79 | 3 | 3.2<br>3.0 | 2.6<br>2.3 | 3.0<br>2.6 | 2.5 | 0.4 |

**Notes**

1. Terminal dimensions within this zone are uncontrolled.
2. Both recesses are ∅ 2.5 × 0.8 max. depth

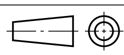
| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT186A | | 3-lead TO-220F | | |  | ~~02-04-09~~<br>06-02-14 |

**Fig 18. Package outline SOT186A (TO-220F)**

## 9. Revision history

**Table 8. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| PSMN016-100XS v.4 | 20120306 | Product data sheet | - | PSMN016-100XS v.3 |
| Modifications: | • Status changed from preliminary to product.<br>• Various changes to content. | | | |
| PSMN016-100XS v.3 | 20111021 | Preliminary data sheet | - | PSMN016-100XS v.2 |

# 10. Legal information

## 10.1 Data sheet status

| Document status[1] [2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URLhttp://www.nxp.com.

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## 11. Contact information

For more information, please visit:http://www.nxp.com

For sales office addresses, please send an email to:salesaddresses@nxp.com

## 12. Contents





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